

Manual Codes (EPI/S-X): U11-C04D

Derwent Registry Numbers: 0245-U; 0270-U; 0306-U; 0323-U; 0325-U; 0335-U;  
0366-U; 0367-U; 0377-U; 0804-U; 0862-U; 0879-U; 0904-U; 1066-U; 1713-U;  
1740-U; 1881-U

21/9/2

DIALOG(R)File 351:DERWENT WPI

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010876091

WPI Accession No: 96-373042/199638

XRAM Accession No: C96-118423 XRPX Accession No: N96-313866

Method of making photoresist compsn. with reduced solvent waste -  
comprising fractionation of polymeric binder resin(s) with supercritical  
fluid, and admixture of resin(s) with photoresist cpd(s).

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Number of Countries: 004 Number of Patents: 002

Patent Family:

Patent No	Kind	Date	Applicat No	Kind	Date	Main IPC	Week
EP 727711	A2	19960821	EP 96300988	A	19960213	G03F-007/004	199638 B
JP 8248633	A	19960927	JP 9628793	A	19960216	G03F-007/032	199649

Priority Applications (No Kind Date): US 95390002 A 19950217

Patent Details:

Patent Kind Lan Pg Filing Notes Application Patent

EP 727711 A2 E 9

Designated States (Regional): DE FR NL

JP 8248633 A 9

Abstract (Basic): EP 727711 A

A method of making a photoresist compsn. comprises:

(a) fractionating polymeric binder resin(s) with a supercritical fluid  
; and

(b) admixing or reacting the fractionated polymeric binder resin with  
photoresist cpd(s). (P).

Cpd. (P) comprises:

(i) a photo [sic: photoactive] cpd.; and/or

(ii) photo acid generator(s).

USE - Compsns. are esp. used in positive-working photoresist for  
processing of Si wafer or GaAs wafer to form semiconductor devices.

ADVANTAGE - Prodn. of solvent waste is reduced or eliminated. Photo acid  
generators (PAG) increase dissolution rate of photoresist films to make  
positive-tone photoimage. Pref. supercritical fluid (SCF) is CO2  
which is safe, non-toxic, inexpensive and readily commercially available.

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Title Terms: METHOD; PHOTORESIST ; COMPOSITION; REDUCE; SOLVENT; WASTE;  
COMPRISE; FRACTIONATE; POLYMERISE; BIND; RESIN; SUPERCRITICAL; FLUID;  
ADMIXED; RESIN; PHOTORESIST ; COMPOUND

Derwent Class: A21; A89; G06; L03; P84; U11

International Patent Class (Main): G03F-007/004; G03F-007/032

International Patent Class (Additional): C08L-061/06; G03F-007/039;

H01L-021/027

File S gment: CPI; EPI; EngPI

## Photoresist compositions containing supercritical fluid fractionated polymeric binder resins

Patent Number: EP0727711  
Publication date: 1996-08-21  
Inventor(s): JEFFRIES ALFRED T III (US); TOUKHY MEDHAT A (US)  
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Requested Patent: EP0727711, A2, A3  
Application Number: EP19960300988 19960213  
Priority Number(s): US19950390002 19950217  
IPC Classification: G03F7/004  
EC Classification: G03F7/023P, G03F7/023P2  
Equivalents: JP8248633  
Cited Documents: WO9312055; EP0623633; EP0615163; GB2242434; JP62121754

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### Abstract

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A photoresist composition comprising either an admixture or a reaction product of: (a) at least one photosensitive compound selected from the group consisting of a photoactive compound, photo acid generators, and mixtures thereof; and (b) at least one polymeric binder resin fractionated with a supercritical fluid.

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